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最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T _b =25°C)					電気的特性 (T _b =25°C)										外形	備考
				V _{ceo} (V)	V _{ceo} (V)	I _c (mA)	P _c (mW)	T _j (°C)	I _{ceo} 最大値 (μA)	直流又はパルスI _{BE}		バイアス		h _{FE}	h _{FE} h _{FE} * (Ω)	h _{FE} h _{FE} * (×10 ⁻⁴)	h _{FE} h _{FE} * (μS)	f _{αb} f _r * (Mc)		
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
 - 9 f_{αb} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_r.
 - 10 C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
 - 11 OUTLINE
 - 12 REMARKS
- :とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 気 的 特 性 (T _a = 25°C)											外形	備考		
				V _{CEO} (V)	V _{EB0} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CEO} 最大値		直流又はパルス hFE		バイアス		h _{FE} *	h _{ic} h ₁₃ * (Ω)	h _{re} h ₁₂ * (×10 ⁻⁴)	h _{oe} h _{ob} * (μU)	f _{βT} * (Mc)			C _{ob} (pF)	F _{βH} h _{ic(real)} * (Ω)
									(μA)	V _{CEB} (V)	V _{CE} (V)	I _C (mA)	V _{CEB} (V)	I _E (mA)									
★ 2SC1421	富士通	RF	Si. EP	15	3	30	250	150	0.5	10	80	6	10	6	-10	NF = 6 dB (f = 2GHz, I _C = 4mA)	5500*	0.7	25*	199			
" 1422	"	"	"	15	3	40	250	150	0.5	10	80	6	20	6	-20		"	5500*	0.8	25*	199		
★ " 1423	"	"	"	15	3	30	250	150	0.5	10	80	6	15	6	-15	NF = 3.5dB (f = 2GHz, I _C = 4mA)	7000*	0.7	25*	199			
" 1424	日電	"	Si. E	30	3	50	250	200	0.1	15	80	10	10	10	-10		G _p = 15dB (f = 500MHz)	2000*	1.1		50C		
" 1425	"	PA	"	45	3	1A	11.6W (T _c = 35°C)	200	100	30	15-250	10	300			G _p = 5 dB (f = 1GHz, V _{cc} = 18V, P _i = 1W)				184			
" 1426	"	RF	"	35	3	200	3.5W (T _c = 25°C)	200	0.1	20	100	10	50	10	-50			2700*	1		85B		
" 1427	"	RF. Conv. Mix. Osc.	"	30	4	10	100	125	0.1	25	120	6	2	6	-2		1000*	0.7	C _c F _{ob} 300pS	176			
" 1428	"	"	"	50	5	50	150	125	0.1	15	110	3	0.5	6	-1		250*	1.5	C _c F _{ob} 25pS	176			
" 1429	ソニー	PA	Si. E PaMe	16	6	2A	950	120	0.1	16	200	2	100	2	-10		80*	26	C _c F _{ob} 300pS	174			
" 1430	"	RF. PA	Si. EMe	110		1.5A	500	150	100	50	100	2	400	2	-200		50*	50	C _c F _{ob} 25pS	181			
" 1431	"	"	"	110	5	2A	1.5W	150	10	50	100	2	400	2	-100		80*	25	C _c F _{ob} 25pS	99			
" 1432	新日無	SW	Si. EP	30	10	300	300	125	1	20	40,000	6	100			t _{on} < 600nS, t _{off} < 1.2μS t _{stg} < 600nS				138	2SA796 とコンパリ		
★ " 1433	東芝	PA. SW	Si. TMe	600	5	5A	50W (T _c = 25°C)	150	100	500	20-300	5	1A	50		t _{on} < 2μS, t _f < 1.5μS t _{stg} < 10μS		100		102			
★ " 1434	"	"	"	600	5	15A	150W (T _c = 25°C)	150	500	500	30-300	5	3A	50		t _{on} < 2μS, t _f < 2.5μS t _{stg} < 15μS		200		102			
★ " 1435	"	"	"	600	5	40A	300W (T _c = 25°C)	150	1mA	500	30-300	5	10A	50		t _{on} < 11μS, t _f < 1.5μS t _{stg} < 10μS		600		196			
" 1436	サンケン	SW	Si. TMe	230	6	15A	100W (T _c = 25°C)	150	1mA	230	20	4	5A	12	-500	t _r < 1.5μS, t _f < 1μS t _{stg} < 4μS, t _d < 0.5μS		10*		102			
" 1437	"	"	"	230	6	50A	200W (T _c = 25°C)	150	1mA	230	20	4	10A	12	-500	t _r < 1.5μS, t _f < 1μS t _{stg} < 4μS		10*		130			
" 1438	富士通	RF	Si. EP	150	5	50	500	150	1	140	150	5	10	5	-10		130*	3		238			
" 1439	"	"	"	150	5	50	500	150	1	140	150	5	10	5	-10		130*	3		138			
" 1440	サンケン	SW	Si. TMe	150	6	15A	100W (T _c = 25°C)	150	1mA	150	20	4	5A	12	-500	t _r < 1.5μS, t _f < 1μS t _{stg} < 4μS, t _d < 0.5μS		10*		102			
" 1441	"	"	"	200	6	15A	100W (T _c = 25°C)	150	1mA	200	20	4	5A	12	-500	t _r < 1.5μS, t _f < 1μS t _{stg} < 4μS, t _d < 0.5μS		10*		102			
" 1442	"	"	"	150	6	50A	200W (T _c = 25°C)	150	1mA	150	20	4	10A	12	-500	t _r < 1.5μS, t _f < 1μS t _{stg} < 4μS		10*		230			
" 1443	"	"	"	200	6	50A	200W (T _c = 25°C)	150	1mA	200	20	4	10A	12	-500	t _r < 1.5μS, t _f < 1μS t _{stg} < 4μS		10*		230			
" 1444	"	PA	"	80	6	6A	40W (T _c = 25°C)	150	1mA	80	80	4	1A	10	-500	t _r < 1.5μS, t _f < 1μS t _{stg} < 4μS		10*	85	12*	99	2SA764 とコンパリ	
" 1445	"	"	"	100	6	6A	40W (T _c = 25°C)	150	1mA	100	80	4	1A	10	-500		10*	85	12*	99	2SA765 とコンパリ		
★ " 1446	松下	"	Si. TP	300	5	100	10W (T _c = 70°C)	150	100	300	70	10	50	30	-20		55*	8	10	268			
" 1447	東芝	RF. PA	Si. T	300	5	150	20W (T _c = 25°C)	150	1	240	40-170	10	50	50	-20		80*	7	30	268			
★ " 1448	"	"	Si. TMe	150	5	1.5A	25W (T _c = 25°C)	150	20	100	75	10	500	10	-500		5*	50	25	268			
" 1449	日電	PA	Si. E	40	5	2A	10W (T _c = 25°C)	150	0.5	35	90	2	300	5	-100		*55*	20	40*	225			
★ " 1450	松下	"	Si. Me	150	5	400	20W (T _c = 80°C)	150	30	60	70	5	100	10	100		15*	50	25	99	2SA766 とコンパリ		